EM74LVC1G04

Single inverter

1.General Description

The EM74LVC1G04 is a single inverter. Inputs can be driven from either 3.3 V or 5 V devices. This feature allows the use of these devices as translators in mixed 3.3 V and 5 V environments. Schmitt-trigger action at all inputs makes the circuit tolerant of slower input rise and fall times. This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2.Features and Benefits

- Wide supply voltage range from 1.65 V to 5.5 V
- Overvoltage tolerant inputs to 5.5 V
- High noise immunity
- CMOS low power dissipation
- I_{OFF} circuitry provides partial Power-down mode operation
- ±24 mA output drive (V_{CC} = 3.0 V)
- Latch-up performance exceeds 250 mA
- Direct interface with TTL levels
- Complies with JEDEC standard:
  - JESD8-7 (1.65 V to 1.95 V)
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8C (2.7 V to 3.6 V)
  - JESD36 (4.5 V to 5.5 V)
- ESD protection:
  - HBM: ANSI/ESDA/JEDEC JS-001 Class 2 exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C.

3.Ordering information

Table 1. Ordering information

Type number	Topside marking	Package		
		Name	Description	Quantity
EM74LVC1G04GV	V3YW	SOT23-5L	SOT23 package, 5 pins 2.92 mm × 1.6 mm; 1.25 mm (Max) height	3000
EM74LVC1G04GW	V3YW	SOT353	SOT353 package, 5 pins 2.1 mm × 1.25 mm; 1.1 mm (Max) height	3000
EM74LVC1G04GS	V3YW	DFN1x1-6L	DFN1×1 package, 6 pins 1 mm × 1 mm; 0.4 mm (Max) height	3000
EM74LVC1G04GM	V3YW	DFN1x1.45-6L	DFN1.45×1 package, 6 pins 1.45 mm × 1 mm; 0.6 mm (Max) height	3000
EM74LVC1G04GX	V3YW	DFN0.8x0.8-4L	DFN0.8×0.8 package, 5pins 0.8 mm × 0.8 mm; 0.4 mm (Max) height	3000

4.Function diagram

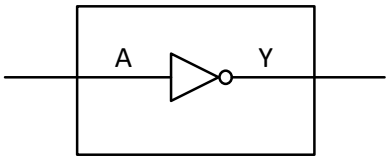


Fig 1. Logic symbol

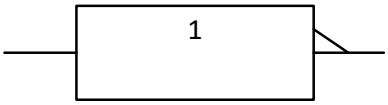


Fig 2. IEC logic symbol

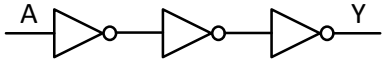


Fig 3. Logic diagram(one gate)

5.Pinning information

5.1. Pin map

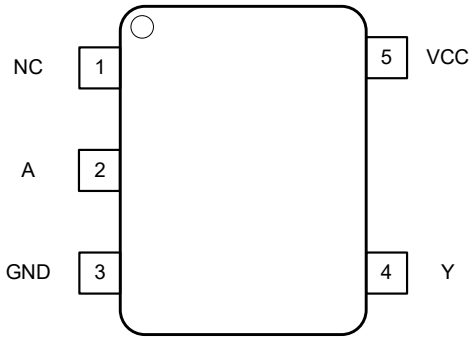


Fig 4. Top view pin configuration SOT23-5 and SOT353

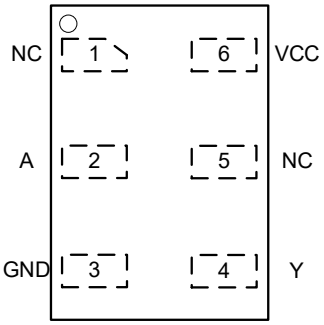


Fig 5. Top view pin configuration DFN6L

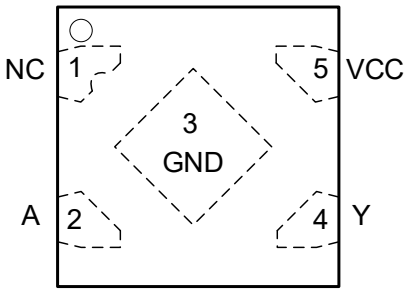


Fig 6. Top view pin configuration DFN4L

5.2. Pin description

Table 2. Pin description

Symbol	Pin		Description
	SOT23-5, SOT353 and DFN4L	DFN6L	
NC	1	1, 5	Not connected
A	2	2	Data input
GND	3	3	Ground (0V)
Y	4	4	Data output
VCC	5	6	Supply voltage

6.Functional description

Table 3. Function table

H = HIGH voltage level; L = LOW voltage level.

Input	Output
A	**Y**
L	H
H	L

7.Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or beoperable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability.The absolute maximum ratings are stress ratings only.

Table 4. Absolute Maximum Ratings

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND.

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	6.5	V
I_{IK}	input clamping current	$V_I < 0$ V	-50		mA
V_I	input voltage	[1]	-0.5	6.5	V
I_{OK}	output clamping current	$V_O > V_{CC}$ or $V_O < 0$ V		±50	mA
V_O	output voltage	Active mode [1]	-0.5	V_{CC} + 0.5	V
		Power-down mode; V_{CC} = 0 V [1]	-0.5	6.5	V
I_O	output current	V_O = 0 V to V_{CC}		±50	mA
I_{CC}	supply current			100	mA
I_{GND}	ground current		-100		mA
P_{tot}	total power dissipation	T_{amb} = -40 °C to + 125 °C		250	mW
T_{stg}	storage temperature		-65	150	°C

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Rhino Semiconductor does not recommend exceeding them or designing to Absolute Maximum Ratings.

Table 5. Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CC}	supply voltage		1.65		5.5	V
V_I	input voltage		0		5.5	V
V_O	output voltage	Active mode	0		V_{CC}	V
		Power-down mode; V_{CC} = 0 V	0		5.5	V
T_{amb}	ambient temperature		-40		125	°C
$\Delta t/\Delta V$	Input transition rise and fall rate	V_{CC} = 1.65 V to 2.7 V			20	ns/V
		V_{CC} = 2.7 V to 5.5 V			10	ns/V

8.Static Characteristics

Table 6. Static characteristics

At recommended operating conditions. Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65V_{CC}			0.65V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7			1.7		V
		V_{CC} = 2.7 V to 3.6 V	2.0			2.0		V
		V_{CC} = 4.5 V to 5.5 V	0.7V_{CC}			0.7V_{CC}		V
V_{IL}	LOW-level input voltage	V_{CC} = 1.65 V to 1.95 V			0.35V_{CC}		0.35V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V			0.7		0.7	V
		V_{CC} = 2.7 V to 3.6 V			0.8		0.8	V
		V_{CC} = 4.5 V to 5.5 V			0.3V_{CC}		0.3V_{CC}	V
V_{OH}	HIGH-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = -100µA; V_{CC} = 1.65 V to 5.5 V	V_{CC} - 0.1			V_{CC} - 0.1		V
		I_O = -4 mA; V_{CC} = 1.65 V	1.2			0.95		V
		I_O = -8 mA; V_{CC} = 2.3 V	1.9			1.7		V
		I_O = -12 mA; V_{CC} = 2.7 V	2.2			1.9		V
		I_O = -24 mA; V_{CC} = 3.0 V	2.3			2.0		V
		I_O = -32 mA; V_{CC} = 4.5 V	3.8			3.4		V
V_{OL}	LOW-level output voltage	V_I = V_{IH} or V_{IL}						
		I_O = 100µA; V_{CC} = 1.65 V to 5.5 V			0.10		0.10	V
		I_O = 4 mA; V_{CC} = 1.65 V			0.45		0.70	V
		I_O = 8 mA; V_{CC} = 2.3 V			0.30		0.45	V
		I_O = 12 mA; V_{CC} = 2.7 V			0.40		0.60	V
		I_O = 24 mA; V_{CC} = 3.0 V			0.55		0.80	V
		I_O = 32 mA; V_{CC} = 4.5 V			0.55		0.80	V
I_I	Input leakage current	V_I = 5.5 V or GND ; V_{CC} = 0 V to 5.5 V		±0.1	±1		±1	µA
I_{OFF}	power-off leakage current	V_{CC} = 0V ; V_I or V_O = 5.5 V		±0.1	±2		±2	µA

I_{CC}	supply current	V_I = 5.5V or GND ; I_O = 0A ; V_{CC} = 1.65V to 5.5V		0.1	4		4	μA
ΔI_{CC}	additional supply current	per pin ; V_{CC} = 2.3V to 5.5V ; V_I = V_{CC} -0.6V ; I_O = 0A		5	500		500	μA
C_I	input capacitance	V_{CC} = 3.3V ; V_I = GND to V_{CC}		5				pF

[1]All typical values are measured at V_{CC} = 3.3V and T_{amb} = 25℃.

9.Dynamic Characteristics

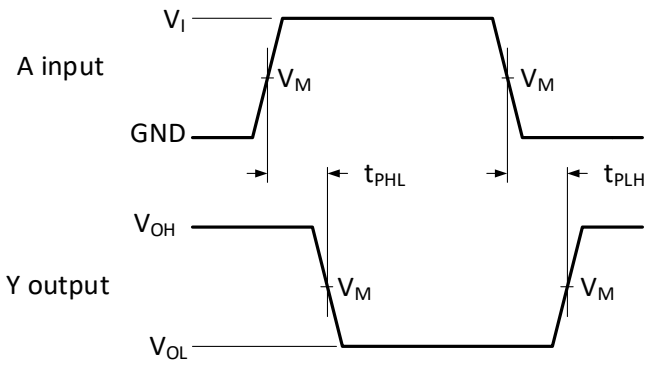
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 8.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	A to Y; see Fig. 7 [2]						
		V_{CC} = 1.65 V to 1.95 V	1.0	3.5	8.0	1.0	9.5	ns
		V_{CC} = 2.3 V to 2.7 V	1.0	2.2	4.4	1.0	5.4	ns
		V_{CC} = 2.7 V	1.0	2.7	5.2	1.0	7.0	ns
		V_{CC} = 3.0 V to 3.6 V	0.5	2.7	4.1	0.5	5.5	ns
		V_{CC} = 4.5 V to 5.5 V	1.0	1.9	3.2	1.0	3.8	ns
C_{PD}	power dissipation capacitance	V_I = GND to V_{CC} ; V_{CC} = 3.3V [3]		14				pF

[1] Typical values are measured at T_{amb} = 25 °C and V_{CC} = 1.8 V, 2.5 V, 2.7 V, 3.3 V and 5.0 V respectively.
[2] t_{pd} is the same as t_{PLH} and t_{PHL}.
[3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:
f_i = input frequency in MHz;
f_o = output frequency in MHz;
C_L = output load capacitance in pF;
V_{CC} = supply voltage in V;
N = number of inputs switching;
$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

9.1. Waveforms and test circuit

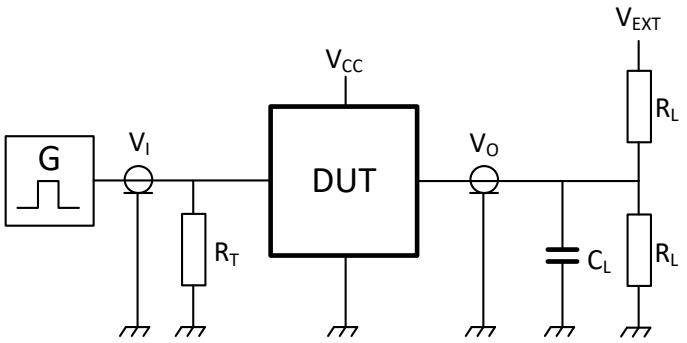


Measurement points are given in Table 8.
V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 7. The input A to output Y propagation delays

Table 8. Measurement points

Supply voltage	Input	Output
V_{CC}	V_M	V_M
1.65 V to 1.95 V	$0.5V_{CC}$	$0.5V_{CC}$
2.3 V to 2.7 V	$0.5V_{CC}$	$0.5V_{CC}$
2.7 V	1.5 V	1.5 V
3.0 V to 3.6 V	1.5 V	1.5 V
4.5 V to 5.5 V	$0.5V_{CC}$	$0.5V_{CC}$



Test data is given in Table 9.
Definitions for test circuit:
R_L = Load resistance.
C_L = Load capacitance including jig and probe capacitance.
R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.
V_{EXT} = External voltage for measuring switching times.

Fig 8. Test circuit for measuring switching times

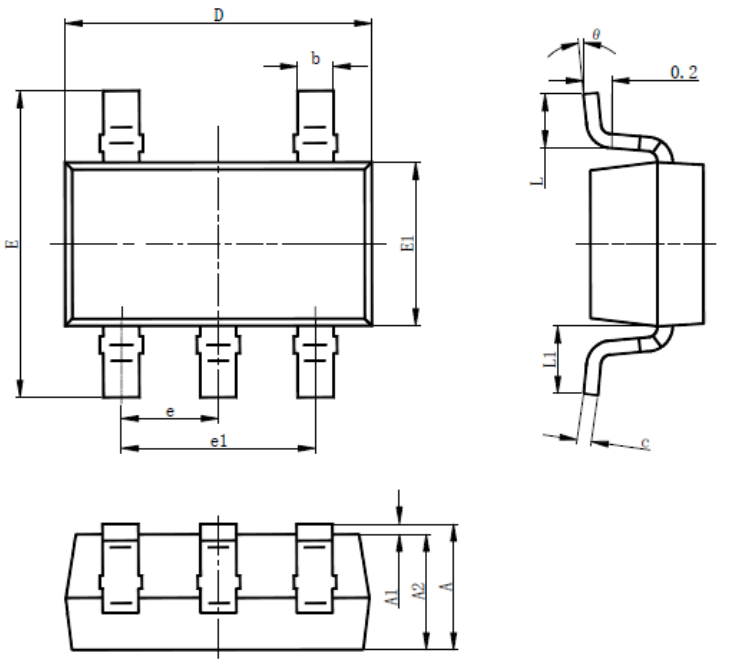
Table 9. Test data

Supply voltage	**Input**		**Load**		**V_{EXT}**
V_{CC}	**V_I**	**$t_r = t_f$**	**C_L**	**R_L**	**t_{PLH}, t_{PHL}**
1.65 V to 1.95 V	V_{CC}	≤ 2.0 ns	30 pF	1 kΩ	open
2.3 V to 2.7 V	V_{CC}	≤ 2.0 ns	30 pF	500 Ω	open
2.7 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
3.0 V to 3.6 V	2.7 V	≤ 2.5 ns	50 pF	500 Ω	open
4.5 V to 5.5 V	V_{CC}	≤ 2.5 ns	50 pF	500 Ω	open

10. Package outline

SOT23-5

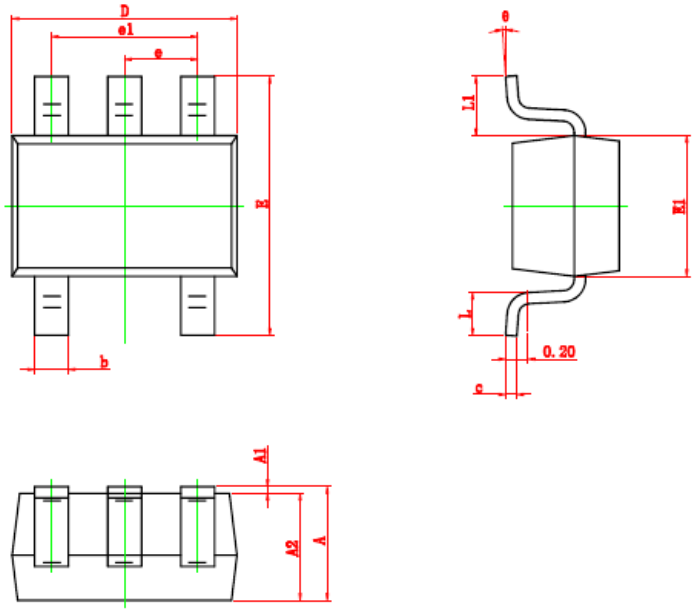
SOT-23-5L(14RZ) PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
L1	0.600REF.		0.024REF.	
θ	0°	8°	0°	8°

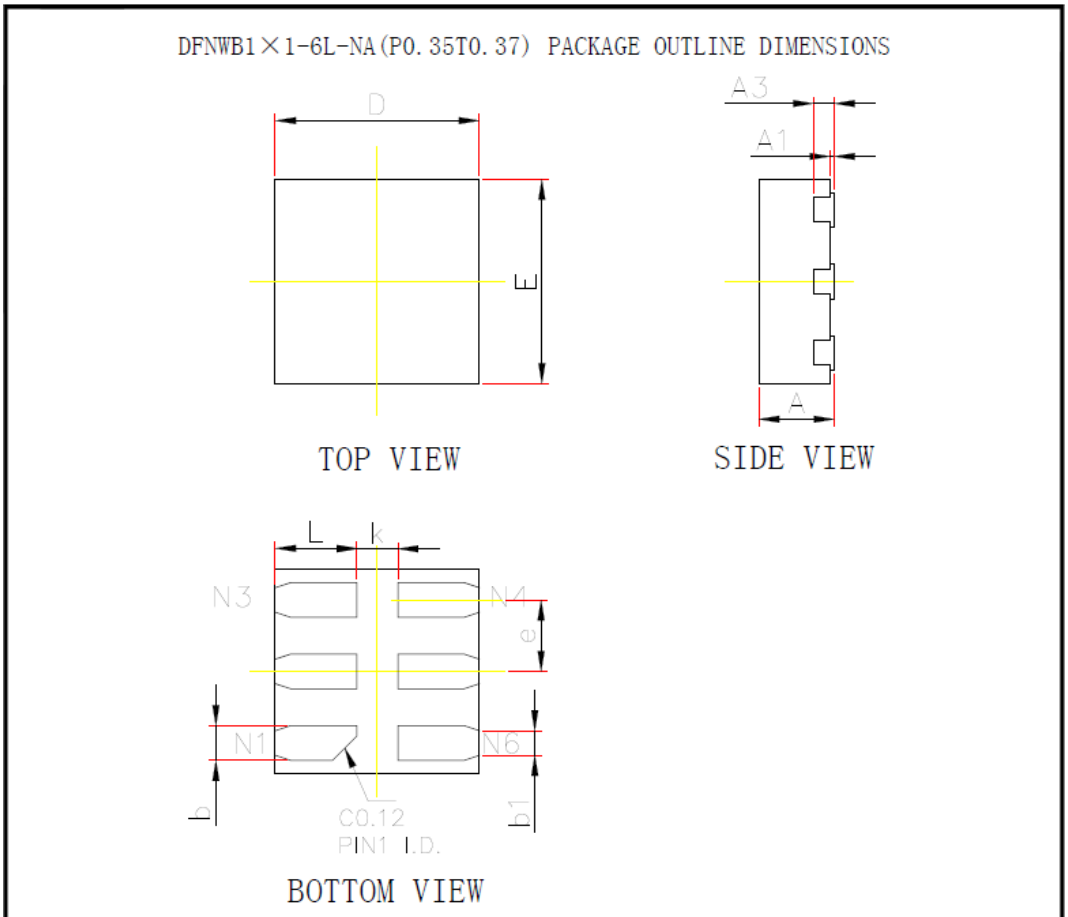
SOT353

SOT-353(16R) PACKAGE OUTLINE DIMENSIONS



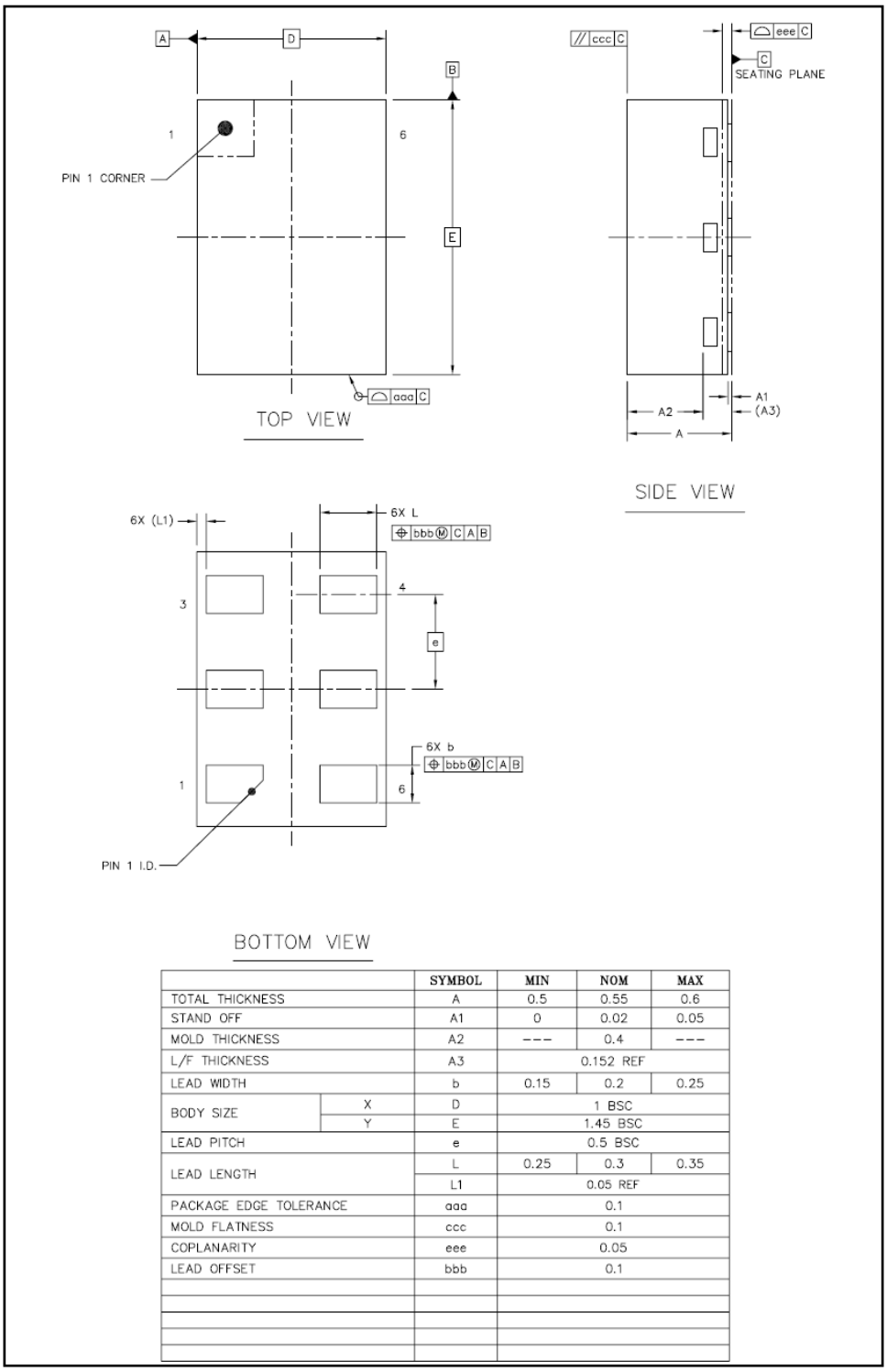
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.150	0.350	0.006	0.014
c	0.110	0.175	0.004	0.007
D	2.000	2.200	0.079	0.087
E	2.150	2.450	0.085	0.096
E1	1.150	1.350	0.045	0.053
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.260	0.460	0.010	0.018
L1	0.525 REF.		0.021 REF.	
θ	0°	8°	0°	8°

DFN1x1-6



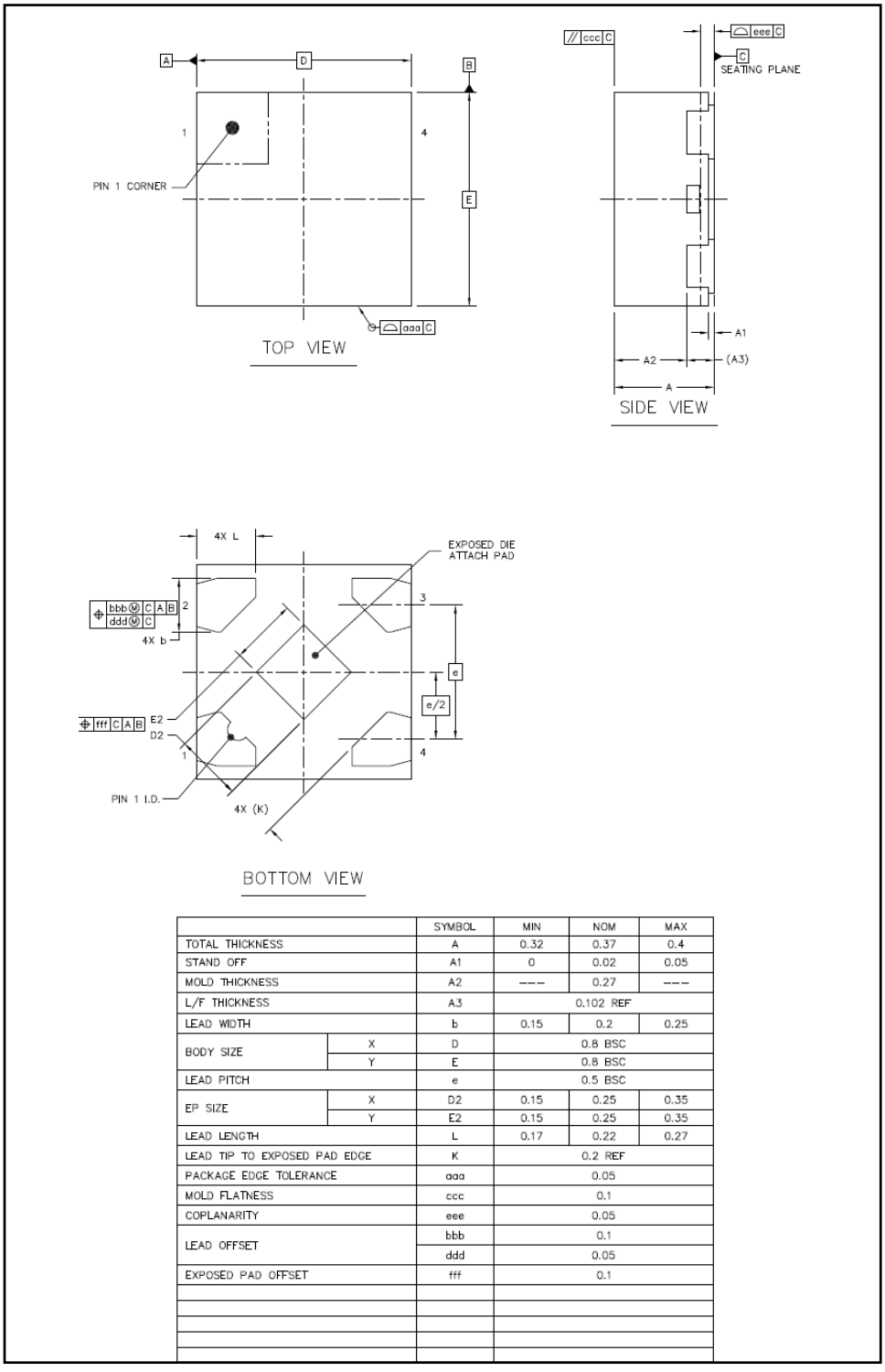
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.320	0.400	0.013	0.016
A1	0.000	0.050	0.000	0.002
A3	0.102REF.		0.004REF.	
D	0.900	1.100	0.035	0.043
E	0.900	1.100	0.035	0.043
k	0.200 REF.		0.008 REF.	
b	0.120	0.220	0.005	0.009
b1	0.120REF.		0.005REF.	
e	0.350BSC.		0.014BSC.	
L	0.350	0.450	0.014	0.018

DFN1.45x1-6



		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.5	0.55	0.6
STAND OFF		A1	0	0.02	0.05
MOLD THICKNESS		A2	---	0.4	---
L/F THICKNESS		A3		0.152 REF	
LEAD WIDTH		b	0.15	0.2	0.25
BODY SIZE	X	D		1 BSC	
	Y	E		1.45 BSC	
LEAD PITCH		e		0.5 BSC	
LEAD LENGTH		L	0.25	0.3	0.35
		L1		0.05 REF	
PACKAGE EDGE TOLERANCE		aaa		0.1	
MOLD FLATNESS		ccc		0.1	
COPLANARITY		eee		0.05	
LEAD OFFSET		bbb		0.1	

DFN0.8x0.8-5



		SYMBOL	MIN	NOM	MAX
TOTAL THICKNESS		A	0.32	0.37	0.4
STAND OFF		A1	0	0.02	0.05
MOLD THICKNESS		A2	---	0.27	---
L/F THICKNESS		A3		0.102 REF	
LEAD WIDTH		b	0.15	0.2	0.25
BODY SIZE	X	D		0.8 BSC	
	Y	E		0.8 BSC	
LEAD PITCH		e		0.5 BSC	
EP SIZE	X	D2	0.15	0.25	0.35
	Y	E2	0.15	0.25	0.35
LEAD LENGTH		L	0.17	0.22	0.27
LEAD TIP TO EXPOSED PAD EDGE		K		0.2 REF	
PACKAGE EDGE TOLERANCE		aaa		0.05	
MOLD FLATNESS		ccc		0.1	
COPLANARITY		eee		0.05	
LEAD OFFSET		bbb		0.1	
		ddd		0.05	
EXPOSED PAD OFFSET		fff		0.1	

11. Abbreviations

Table 10. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

12. Revision history

Table 11. Revision history

Document ID	Release Date	Data sheet status	Change notice	Supersedes
EM74LVC1G04 Rev0.1	Apr 03, 2023	Draft datasheet	Preliminary draft version	

1